



DMG2305UXQ

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	Package	I _D T _A = +25°C
-20V	$52m\Omega @V_{GS} = -4.5V$	SOT23	-5.0A
-200	100mΩ @V _{GS} = -2.5V	30123	-3.6A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- **Power Management Functions**
- DC-DC Converters
- Motor Control

Features

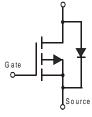
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability
- PPAP capable (Note 4)

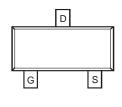
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)









Top View

Internal Schematic

Top View

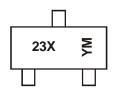
Ordering Information (Note 5)

Part Number Compliance		Case	Packaging
DMG2305UXQ-7	Standard	SOT23	3,000/Tape & Reel
DMG2305UXQ-13	Standard	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



23X = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009)M = Month (ex: 9 = September)

Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		X		Υ		<u>Z</u>	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V _{DSS}	-20	V	
Gate-Source Voltage	V _{GSS}	±8	V		
Continuous Drain Current (Note C) V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	l _D	-4.2 -3.3	А
Continuous Drain Current (Note 6) V _{GS} = -4.5V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-5.0 -4.0	А
Pulsed Drain Current (Note 7)		I _{DM}	-10	Α	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 6)	P_{D}	1.4	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	2	90	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	64	°C/W
Thermal Resistance, Junction to Case (Note 8)	R ₀ JC	33	°C/W	
Operating and Storage Temperature Range		T_J, T_STG	-55 to +150	°C

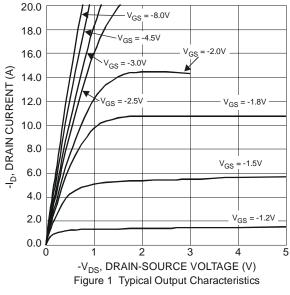
Electrical Characteristics (@T_A = ±25°C, unless otherwise specified.)

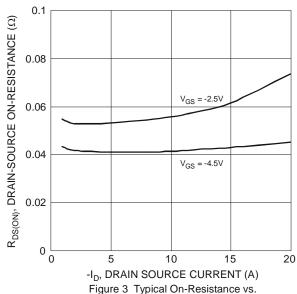
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV_{DSS}	-20	_		V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	_	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			40	52		$V_{GS} = -4.5V$, $I_{D} = -4.2A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	52	100	mΩ	$V_{GS} = -2.5V$, $I_{D} = -3.4A$	
			68	200		$V_{GS} = -1.8V, I_D = -2A$	
Forward Transfer Admittance	Y _{fs}	_	9	_	S	$V_{DS} = -5V, I_{D} = -4A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	808	_	pF		
Output Capacitance	Coss	_	85	_	pF	$V_{DS} = -15V, V_{GS} = 0V$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	77	_	pF	1 = 1.0WH IZ	
Gate Resistance	Rg		15.2		Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$	
SWITCHING CHARACTERISTICS (Note 9)							
Total Gate Charge	Q_g	_	10.2	_	nC	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Gate-Source Charge	Q_{gs}	_	1.3	_	nC	$V_{GS} = -4.5V, V_{DS} = -4V,$ $-I_{D} = -3.5A$	
Gate-Drain Charge	Q_{gd}	_	2.2	_	nC	ID = -3.5A	
Turn-On Delay Time	t _{D(on)}	_	10.8	_	nS		
Turn-On Rise Time	t _r		13.7		nS	$V_{DS} = -4V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t _{D(off)}	_	79.3	_	nS	$R_G = 6\Omega$, $I_D = -1A$	
Turn-Off Fall Time	t _f	_	34.7	_	nS	<u> </u>	

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

^{7.} Repetitive rating, pulse width limited by junction temperature.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing







Drain Current and Gate Voltage

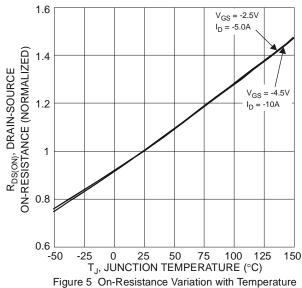


Figure 5 On-Resistance Variation with Temperature

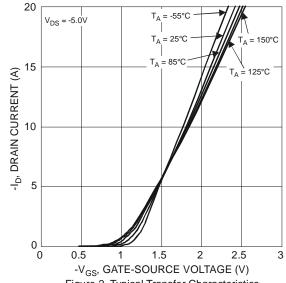
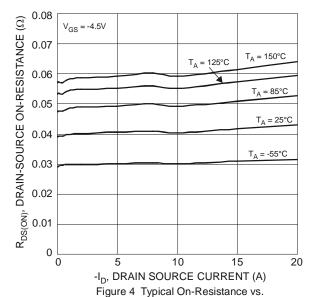


Figure 2 Typical Transfer Characteristics



Drain Current and Temperature

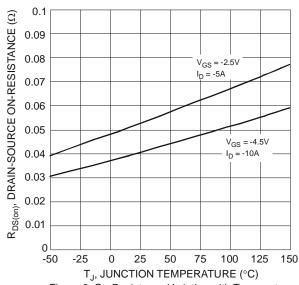


Figure 6 On-Resistance Variation with Temperature



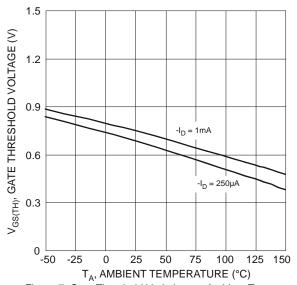
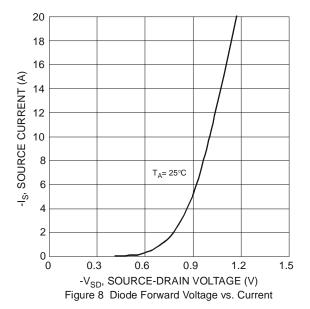


Figure 7 Gate Threshold Variation vs. Ambient Temperature

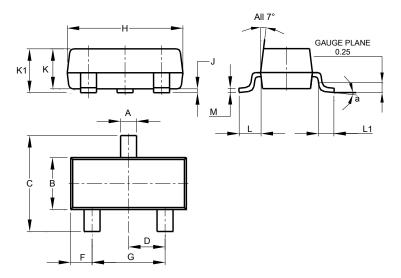




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

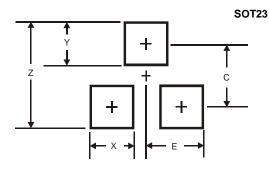
SOT23



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	H 2.80		2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	a 8°					
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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